

BD235/BD236 BD237/BD238

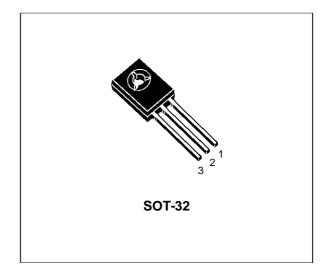
COMPLEMENTARY SILICON POWER TRANSISTORS

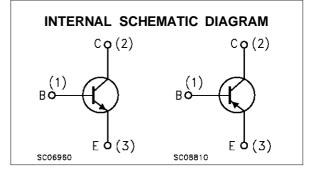
SGS-THOMSON PREFERRED SALESTYPES

DESCRIPTION

The BD235 and BD237 are silicon epitaxial-base NPN power transistors in Jedec SOT-32 plastic package inteded for use in medium power linear and switching applications.

The complementary PNP types are BD236 and BD238 respectively.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Val	Unit	
		NPN	BD235	BD237	
		PNP	BD236	BD238	
V _{CBO}	Collector-Base Voltage (I _E = 0)	60	100	V	
VCER	Collector-Base Voltage ($R_{BE} = 1K\Omega$)		60	100	V
V _{CEO}	Collector-Emitter Voltage $(I_B = 0)$		60	80	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)		5		V
lc	Collector Current		2		Α
I _{CM}	Collector Peak Current		6		Α
Ptot	Total Dissipation at $T_c = 25$ °C		25		W
T _{stg}	Storage Temperature		-65 to 150		°C
Tj	Max. Operating Junction Temperature		150		°C

For PNP types voltage and current values are negative.

THERMAL DATA

Rthj-case Thermal Resistance Junction-case Max 5 °C/W

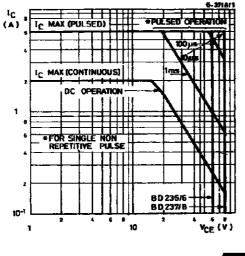
ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \ ^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector Cut-off Current ($I_E = 0$)	V_{CE} = rated V_{CEO} V_{CE} = rated V_{CEO} T_{c} = 150 °C			0.1 2	mA mA
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	V _{EB} = 5 V			1	mA
$V_{CEO(sus)}^{*}$	Collector-Emitter Sustaining Voltage	I _C = 100 mA for BD235/BD236 for BD237/BD238	60 80			V V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_{\rm C} = 1 \ {\rm A}$ $I_{\rm B} = 0.1 \ {\rm A}$			0.6	V
V _{BE} *	Base-Emitter Voltage	I _C = 1 A V _{CE} = 2 V			1.3	V
h _{FE} *	DC Current Gain		40 25			
f⊤	Transition frequency	I _C = 250 mA V _{CE} = 10 V	3			MHz
h _{FE1} /h _{FE2} *	Matched Pairs	$I_{C} = 150 \text{ mA}$ $V_{CE} = 2 \text{ V}$		1.6		

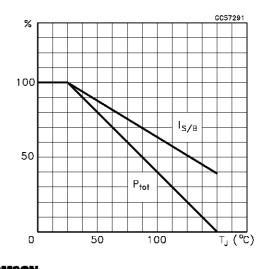
* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

Safe Operating Area

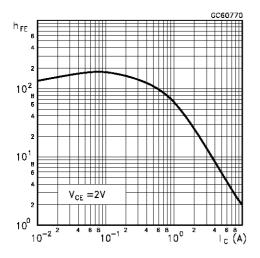
2/5



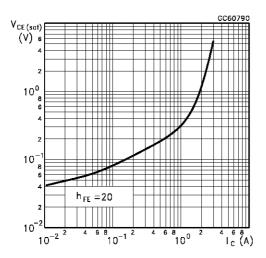
Derating Curves



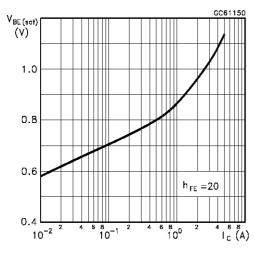
DC Current Gain (NPN type)



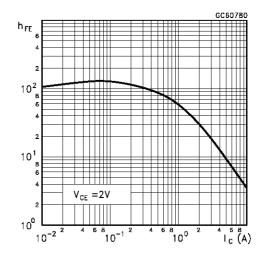
Collector-Emitter Saturation Voltage (NPN type)



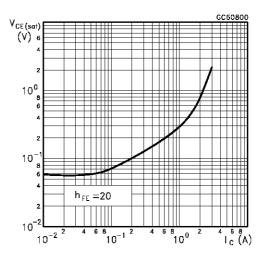
Base-Emitter Saturation Voltage (NPN type)



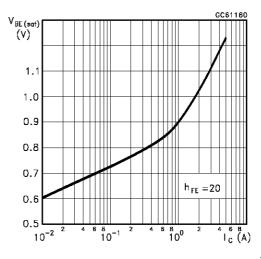
DC Current Gain (PNP type)



Collector-Emitter Saturation Voltage (PNP type)



Collector-Base Capacitance (PNP type)

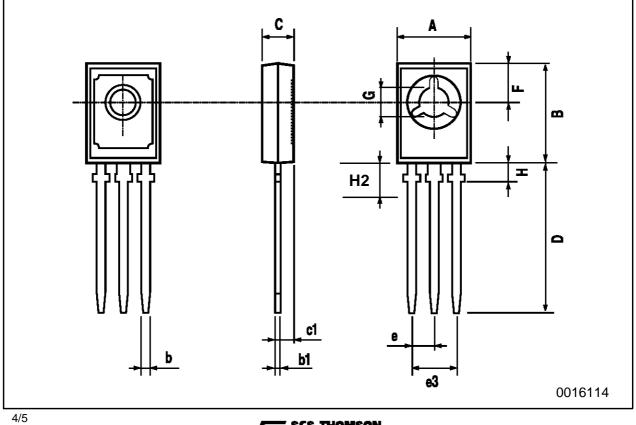




BD235/BD236/BD237/BD238

SOT-32 (TO-126) MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	7.4		7.8	0.291		0.307	
В	10.5		10.8	0.413		0.445	
b	0.7		0.9	0.028		0.035	
b1	0.49		0.75	0.019		0.030	
С	2.4		2.7	0.040		0.106	
c1	1.0		1.3	0.039		0.050	
D	15.4		16.0	0.606		0.629	
е		2.2			0.087		
e3	4.15		4.65	0.163		0.183	
F		3.8			0.150		
G	3		3.2	0.118		0.126	
Н			2.54			0.100	
H2		2.15			0.084		



SGS-THOMSON

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsability for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may results from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectonics.

© 1997 SGS-THOMSON Microelectronics - Printed in Italy - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES Australia - Brazil - Canada - China - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A

